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	Document ID Pages	Pages		5		
			Multi-level type nonvolatile semiconductor memory	257/324	257/295	Miura, Hirotomo et al.
-	US 6469343 B1 20	70	device		257/326.	
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3	US 613//18 A 6	ه .	arrangement	ס	257/520 208	
			Two bit non volatile electrically erasable and	365/185.3	365/185.3 365/131	Fitan Boaz
	115 6011775 A 37	37	programmable semiconductor memory cell utilizing	ಌ	303/131.	
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